Amendments to the Specification

Please replace paragraph [0060] with the following amended paragraph:

[0060] According to another aspect of the present invention, a method of forming a semiconductor device comprises a) forming a first insulating layer on a semiconductor substrate, forming a layer of conductive material on the first insulating layer, and patterning the first conductive layer to form at least one gate pattern, b) forming a second insulating layer on the gate pattern and substrate, c) reducing the thickness of the second insulating layer until the upper surface thereof becomes situated beneath the level of the upper surface of the gate pattern, d) forming a second conductive layer over the resultant structure, e) selectively removing portions of the second conductive layer such that a first spacer of the conductive material is formed at both sides of an upper portion of the gate pattern, f) subsequently removing portions of the second insulating layer other than those located beneath the spacer, g) implanting ions at a relatively low concentration into the substrate at the sides of the gate pattern to form a lightly-doped source/drain region, h) forming a fourth insulating layer over the resultant structure, i) selectively removing portions of the fourth insulating layer to form a second spacer at the sides of the gate pattern, j) subsequently implanting ions at a relatively heavy concentration into the substrate at the sides of the gate pattern to form a heavily-doped source/drain region, k) subsequently heat-treating the substrate to chemically bond the dopants to the substrate, and ~~m~~ l) forming a third conductive layer

Please replace paragraph [0070] with the following amended paragraph:

[0070] Preferably, the fourth insulating layer is formed (h) on the third insulating layer using a CVD or a PVD process, and is subsequently selectively etched (i) using an anisotropic etching process. The heavily concentrated ~~of~~ ions are implanted into the substrate using the enlarged gate pattern and the second spacer as masks.

Please replace paragraph [0075] with the following amended paragraph:

[0075] According to still another aspect of the present invention, a semiconductor device comprises a) a semiconductor substrate, b) a gate insulating layer disposed on the substrate, c) a T- or mushroom-shaped gate electrode including a ~~man~~ main body disposed on the gate insulating layer and wings extending laterally from an upper portion of the main body, ~~e~~ d) a capacitance preventative layer of insulating material disposed under the wings of the T- or mushroom-shaped gate electrode, ~~d~~ e) a discrete spacer disposed at both sides of the gate electrode laterally of the capacitance preventative layer and, ~~e~~ f) a source electrode and a drain electrode defined at opposite sides of the gate electrode.

Please replace paragraph [0085] with the following amended paragraph:

[0085] Preferably, the main body and wings of the gate electrode comprise polysilicon, and the capacitance preventative layer is a low-temperature oxide (LTO). In addition, the semiconductor device of the present invention may further comprise an anti-diffusion layer for preventing ion dopants in the source/drain region of the substrate from diffusing into a channel region located beneath the gate electrode. The gate electrode preferably also comprises a metal silicide layer on the main body and wings thereof to thereby reduce the electrical resistance of the gate electrode. The metal silicide layer may also be disposed on the source/drain electrode to thereby ~~to~~ reduce the electrical resistance thereof.